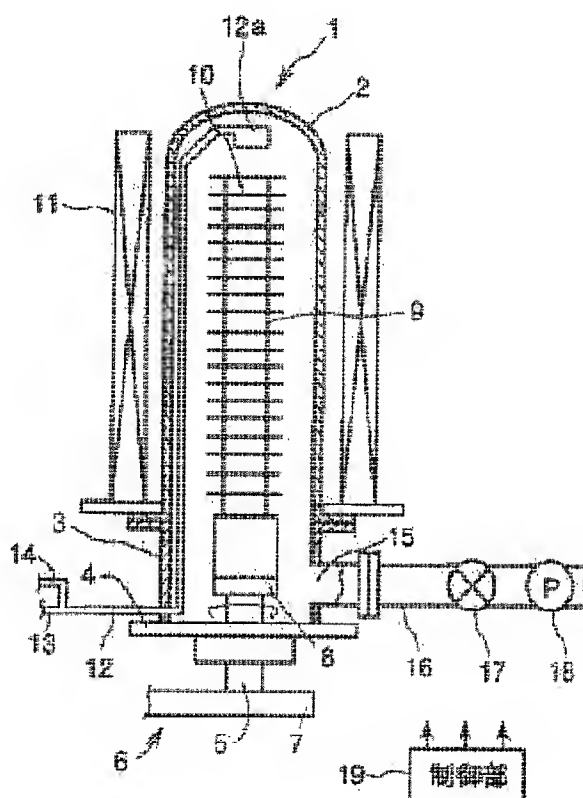


THIN FILM FORMING METHOD AND EQUIPMENT THEREOF**Publication number:** JP2002231716 (A)**Publication date:** 2002-08-16**Inventor(s):** SUZUKI KEISUKE**Applicant(s):** TOKYO ELECTRON LTD**Classification:****- international:** *H01L21/31; H01L21/316; H01L21/02;* (IPC1-7): H01L21/316; H01L21/31**- European:****Application number:** JP20010025170 20010201**Priority number(s):** JP20010025170 20010201**Abstract of JP 2002231716 (A)**

PROBLEM TO BE SOLVED: To provide a thin film forming method and thin film forming equipment which can form a thin film having uniform thickness on an object to be treated. **SOLUTION:** Heat treatment equipment 1 is provided with a reaction tube 2 accommodating a semiconductor wafer 10, a heater 11 for rise of temperature which heats the reaction tube 2, a gas introducing tube 12 for supplying treating gas, and a control unit 19 for controlling them. The control unit 19 makes the heater 11 heat the reaction tube 2, and makes the gas introducing tube 12 supply the treating gas to the reaction tube 2, at a flow rate which can cool the peripheral part of the semiconductor wafer 10.



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